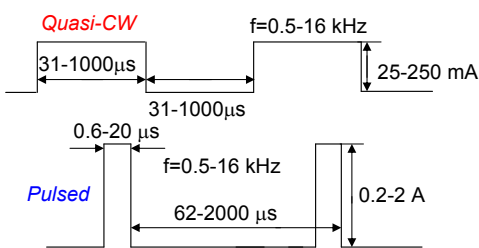
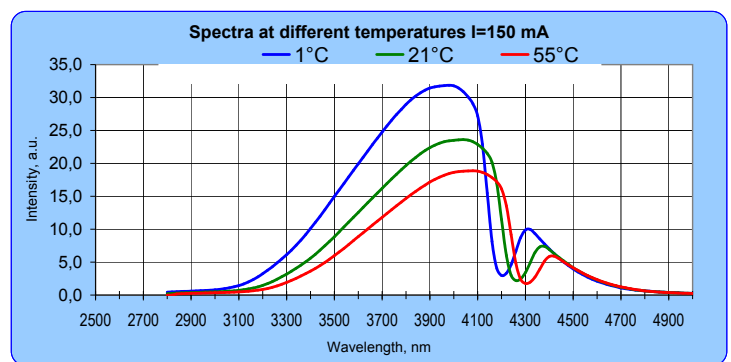
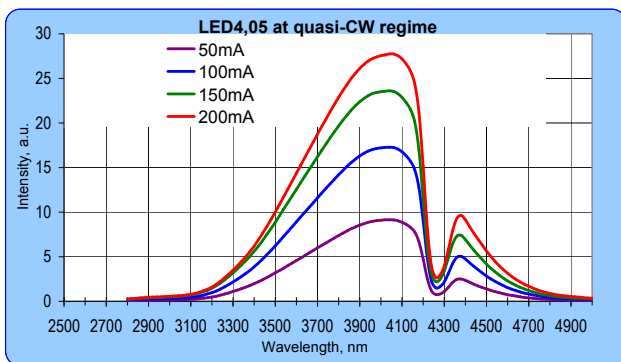


Light Emitting Diodes with central wavelength 4,1  $\mu\text{m}$  series are based on heterostructures grown on InAs substrates by MOCVD. InAsSb is used in the active layer. Wide band gap solid solutions InAsSbP with P content 50% are used for good electron confinement.

Parameters	Units	Conditions	Ratings		
			Min	Typ	Max
Peak emission wavelength	$\mu\text{m}$	T=300 K	3,95	4,05	4,10
FWHM of the emission band	nm	150 mA CW	700	850	1000
Quasi-CW Optical Power	$\mu\text{W}$	200 mA qCW	15	20	30
Pulsed Optical Power	$\mu\text{W}$	1 A	180	200	220
Switching Time	ns	T=300 K	10	20	30
Operating Temperature Range, $^{\circ}\text{C}$	-240 $^{\circ}$ $\div$ +50 $^{\circ}$				
Emitting Area, $\mu\text{m}$	300x300				
Soldering temperature	260 $^{\circ}\text{C}$				
Package					
SMD type package 3x3 mm based on high thermal conductivity ceramics			MID IR LED-SMD3		
SMD type package 5x5 mm based on high thermal conductivity ceramics			<b>MID IR LED-SMD5</b>		
SMD type package 5x5 mm based on high thermal conductivity ceramics with microreflector			MID IR LED-SMD5R		



Maximum current is 220 mA at quasi-CW  
Maximum pulsed current is 1 A (duration 500 ns, repetition rate 2 kHz)  
Optimal operating current is 150-200 mA at quasi-CW.

